[redacted]0GP06A

[redacted]t Mode Field Effect [redacted]ansistor

Product Summary

V_{DS}	[redacted]V
I_D	[redacted]A
$R_{DS(ON)}$(at V_{GS}=-10V)	[redacted]25 mohm
$R_{DS(ON)}$(at V_{GS}=-4.5V)	[redacted]30 mohm
100% EAS Tested	
100% V_{DS} Tested	

General Description

- Split gate trench MOSFET t[redacted]logy
- Low $R_{DS(on)}$ & FOM
- Low Crss
- Extremely low switching loss[redacted]
- Excellent stability and unifor[redacted]
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flam[redacted]lity Rating
- Halogen Free

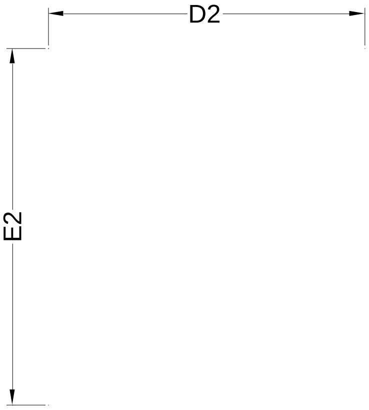
Applications

- Load Switch
- Industrial DC/DC Conversion[redacted]uits

[redacted]erwise noted)

[redacted]	Symbol	[redacted]t	Unit
	V_{DS}		

PDFN5060-8L-B-1.1MM



Top View

Bottom View

Side View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1			

Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.10mm.
3.The pad layout is for reference purposes only.

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